

Abstract

In order to improve a purity of an entire polycrystalline silicon rod, a polycrystalline silicon rod (1) is configured such that: an outer-side total concentration (C1) is 100 pptw
5 or less; and a ratio of an outer-side total concentration (C1) to an inner-side total concentration (C2) is 1.0 or more and 2.5 or less.

Figure 1 accompanies.